

2N65-CBS

Power MOSFET

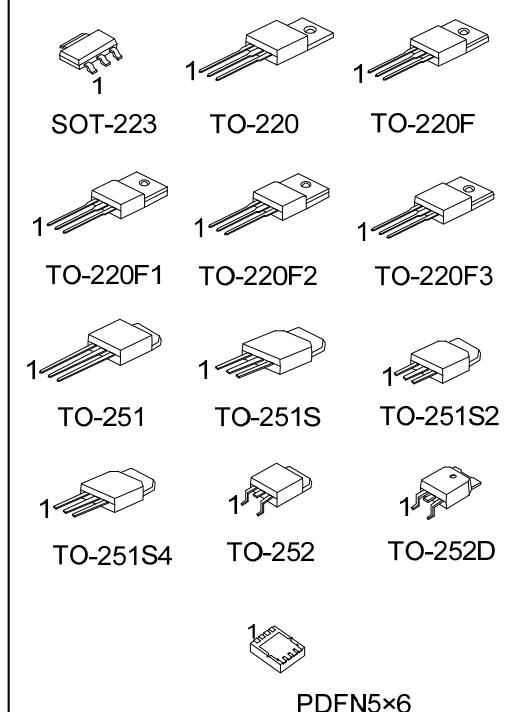
**2.0A, 650V N-CHANNEL
POWER MOSFET**

■ DESCRIPTION

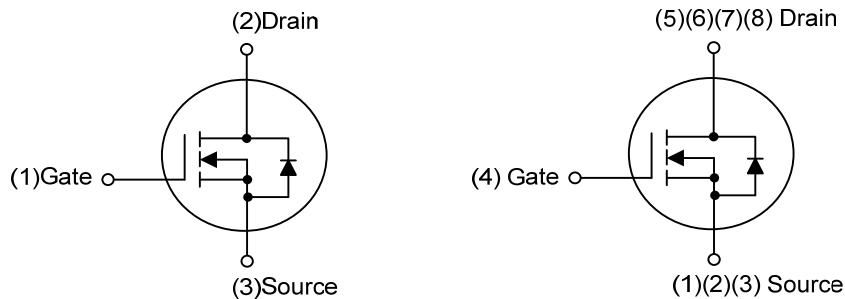
The UTC **2N65-CBS** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

■ FEATURES

- * $R_{DS(ON)} \leq 9.5 \Omega$ @ $V_{GS}=10V$, $I_D=1.0A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



■ SYMBOL



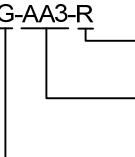
TO-220/TO-220F/TO-220F1/TO-220F2
TO-220F3/TO-251/TO-251S/TO-251S2
TO-251S4/TO-252/TO-252D/SOT-223

PDFN5x6

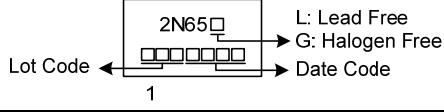
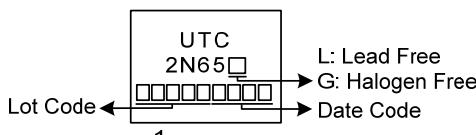
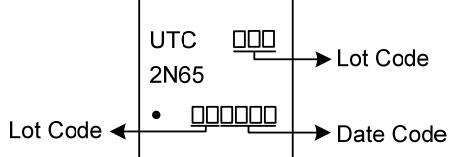
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
2N65L-AA3-R	2N65G-AA3-R	SOT-223	G	D	S	-	-	-	-	-	Tape Reel
2N65L-TA3-T	2N65G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
2N65L-TF3-T	2N65G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	Tube
2N65L-TF1-T	2N65G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
2N65L-TF2-T	2N65G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	Tube
2N65L-TF3T-T	2N65G-TF3T-T	TO-220F3	G	D	S	-	-	-	-	-	Tube
2N65L-TM3-T	2N65G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
2N65L-TMS-T	2N65G-TMS-T	TO-251S	G	D	S	-	-	-	-	-	Tube
2N65L-TMS2-T	2N65G-TMS2-T	TO-251S2	G	D	S	-	-	-	-	-	Tube
2N65L-TMS4-T	2N65G-TMS4-T	TO-251S4	G	D	S	-	-	-	-	-	Tube
2N65L-TN3-R	2N65G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
2N65L-TND-R	2N65G-TND-R	TO-252D	G	D	S	-	-	-	-	-	Tape Reel
2N65L-P5060-R	2N65G-P5060-R	PDFN5×6	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

 (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) AA3: SOT-223, TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF1: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4, TN3: TO-252, TND: TO-252D P5060: PDFN5×6 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

PACKAGE	MARKING
SOT-223	 Lot Code ← 1 → Date Code
TO-220 / TO-220F TO-220F1 / TO-220F2 TO-220F3 / TO-251 TO-251S / TO-251S2 TO-251S4 / TO-252 TO-252D	 Lot Code ← 1 → Date Code
PDFN5×6	 Lot Code ← • → Date Code

■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	1.6	A
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	4	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	25	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.2	V/ns
Power Dissipation	SOT-223	P_D	2	W
	TO-220		45	W
	TO-220F/TO-220F1		15	W
	TO-220F2/TO-220F3			
	TO-251/TO-251S		25	W
	TO-251S2/TO-251S4			
	TO-252/TO-252D		22	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=30\text{mH}$, $I_{AS}=1.3\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 2.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^\circ\text{C/W}$
	TO-220/TO-220F			
	TO-220F1/ TO-220F2		62.5	$^\circ\text{C/W}$
	TO-220F3			
	TO-251/TO-251S		110	$^\circ\text{C/W}$
	TO-251S2/TO-251S4			
	TO-252/TO-252D		75	$^\circ\text{C/W}$
Junction to Case	PDFN5x6	θ_{JC}		
	SOT-223		62.5	$^\circ\text{C/W}$
	TO-220		2.77	$^\circ\text{C/W}$
	TO-220F/TO-220F1		8.33	$^\circ\text{C/W}$
	TO-220F2/TO-220F3			
	TO-251/TO-251S		5 (Note)	$^\circ\text{C/W}$
	TO-251S2/TO-251S4			
TO-252/TO-252D	PDFN5x6		5.7	$^\circ\text{C/W}$

Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

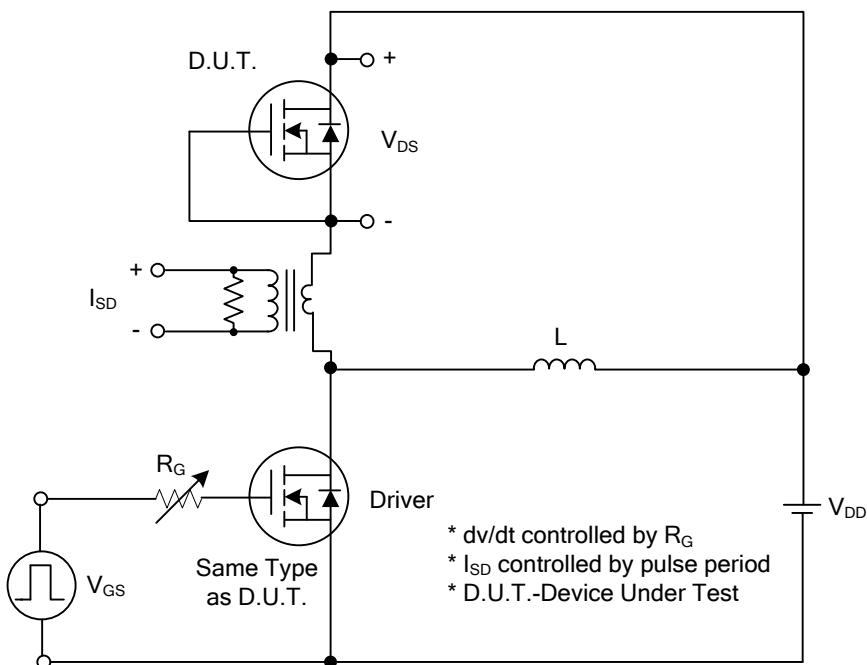
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}} = 650\text{V}, V_{\text{GS}} = 0\text{V}$		10		μA
Gate-Source Leakage Current	Forward	$V_{\text{GS}} = 30\text{V}, V_{\text{DS}} = 0\text{V}$		100		nA
	Reverse	$V_{\text{GS}} = -30\text{V}, V_{\text{DS}} = 0\text{V}$		-100		nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 1.0\text{A}$			9.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		158		pF
Output Capacitance	C_{OSS}			19		pF
Reverse Transfer Capacitance	C_{RSS}			2.1		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{\text{DS}} = 520\text{V}, V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 2\text{A}$ $I_G = 1\text{mA}$ (Note 1, 2)		10		nC
Gate-Source Charge	Q_{GS}			4		nC
Gate-Drain Charge	Q_{GD}			1.5		nC
Turn-On Delay Time	$t_{\text{D}(\text{ON})}$			4		ns
Turn-On Rise Time	t_R			14		ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$			54		ns
Turn-Off Fall Time	t_F			34		ns
DRAIN-SOURCE DIODE CHARACTERISTICS						
Continuous Drain-Source Current	I_S				2.0	A
Pulsed Drain-Source Current	I_{SM}				4.0	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{SD}} = 2.0\text{A}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$V_{\text{GS}} = 0\text{V}, I_{\text{SD}} = 2.0\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		175		ns
Body Diode Reverse Recovery Charge	Q_{rr}			0.7		μC

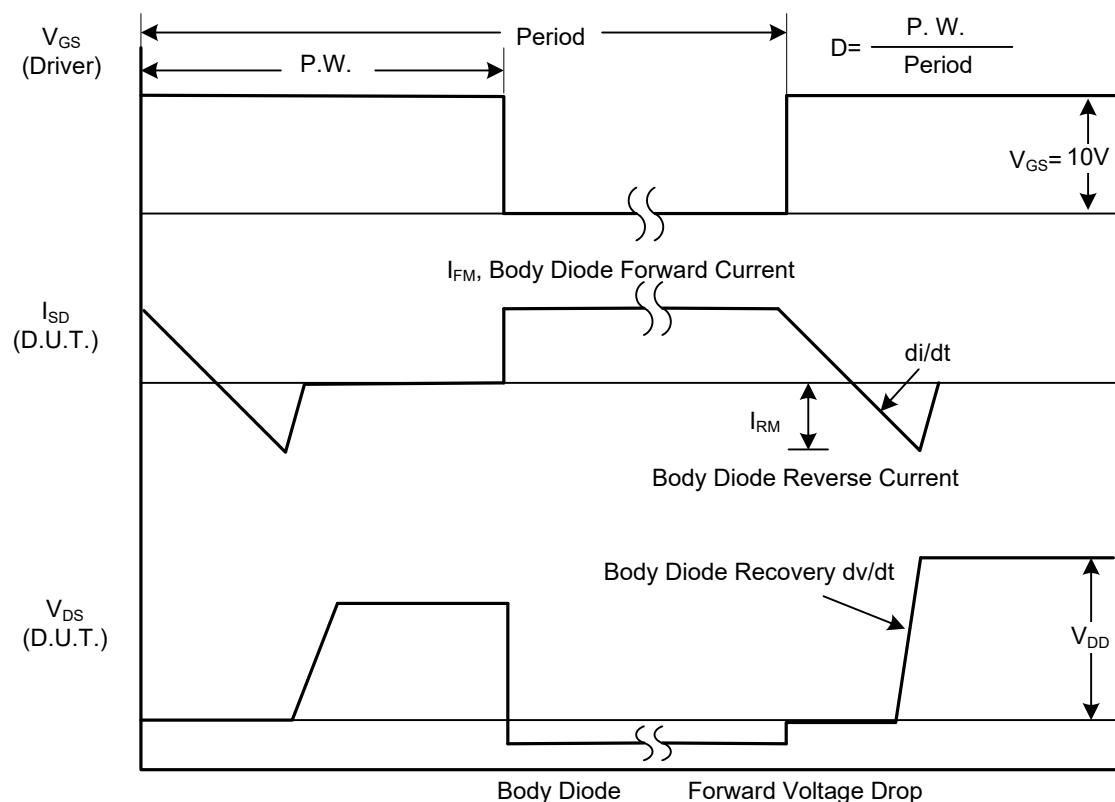
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

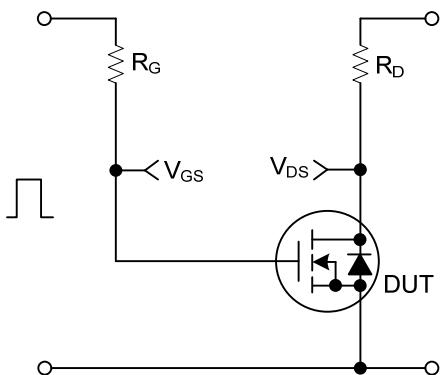


Peak Diode Recovery dv/dt Test Circuit

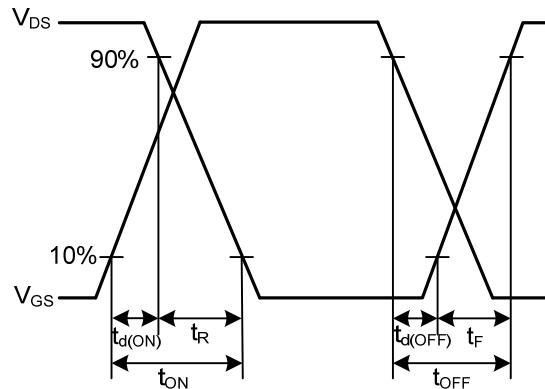


Peak Diode Recovery dv/dt Waveforms

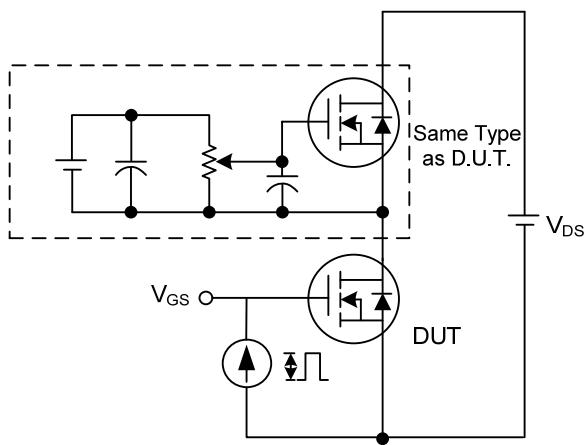
■ TEST CIRCUITS AND WAVEFORMS



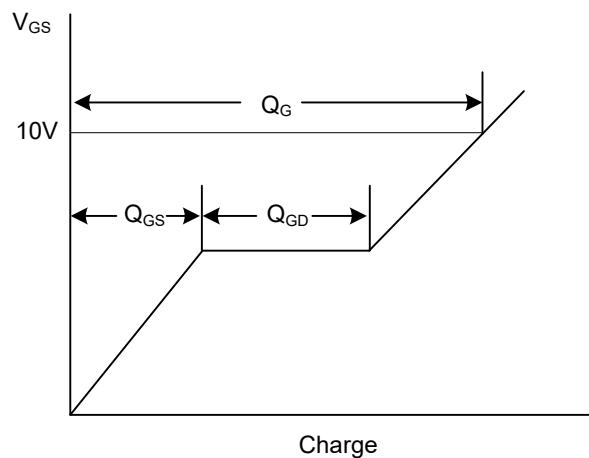
itching Test Circuit



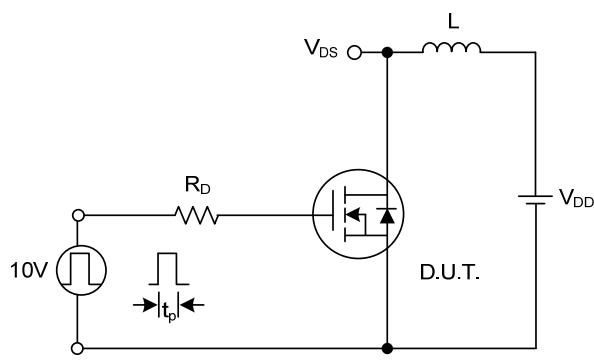
Switching Waveforms



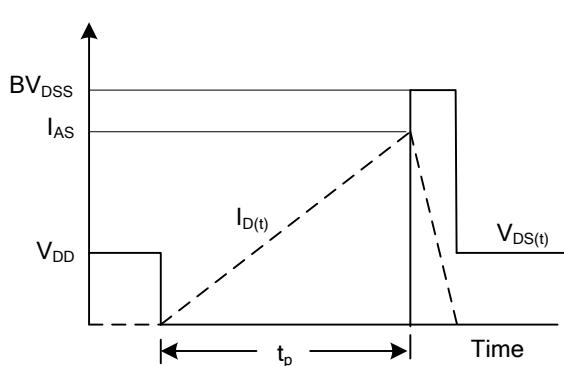
Gate Charge Test Circuit



Gate Charge Waveform

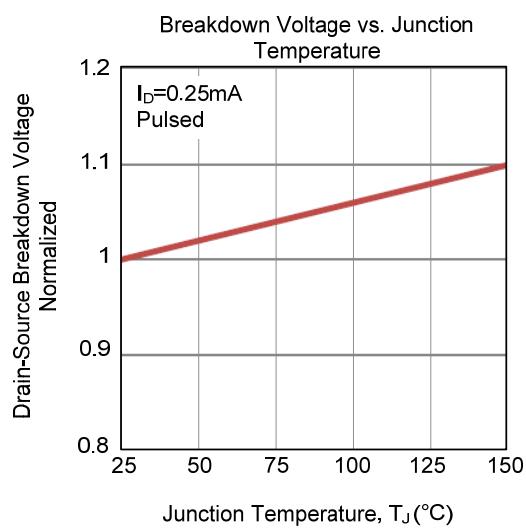
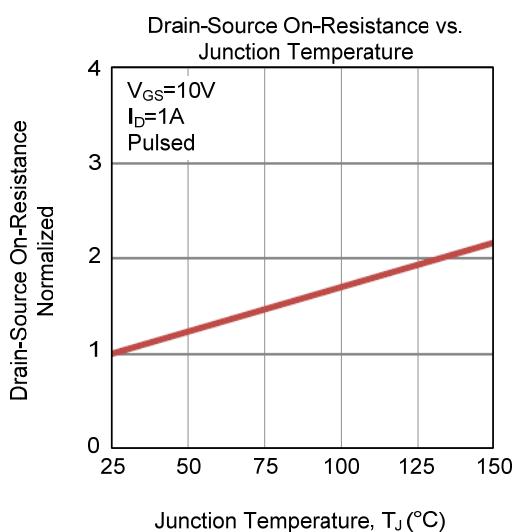
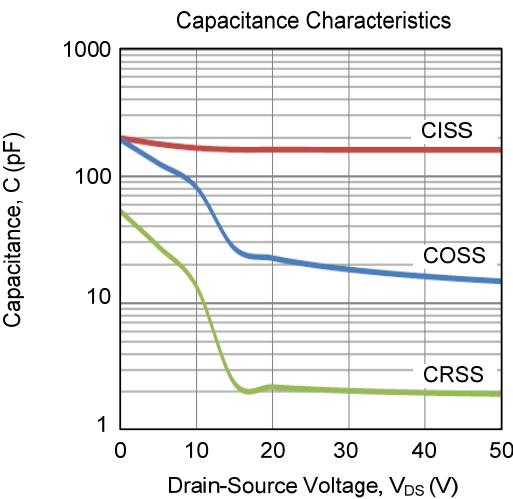
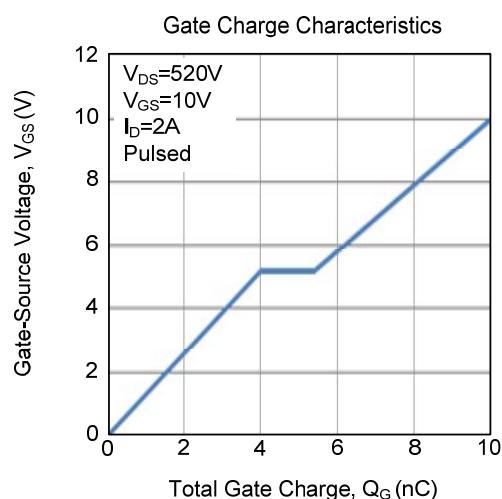
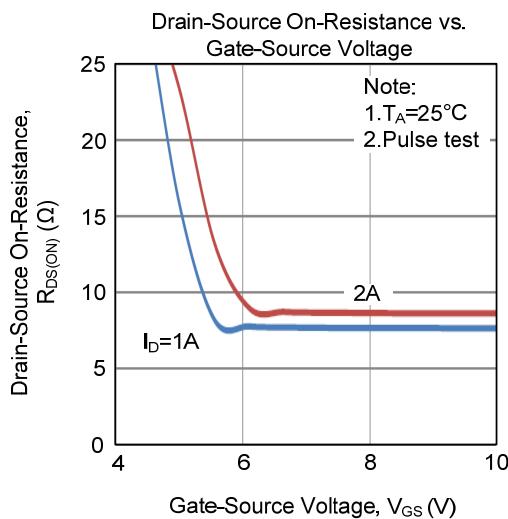
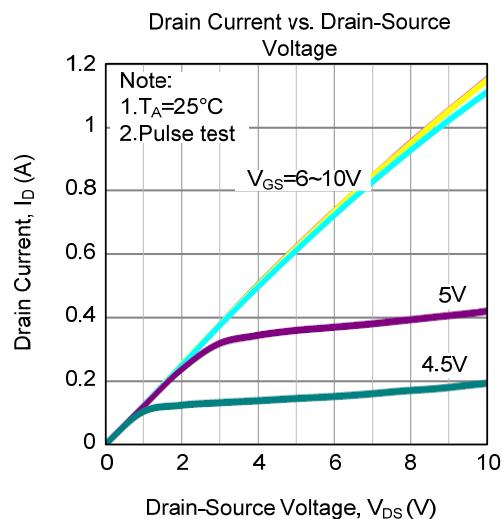


Unclamped Inductive Switching Test Circuit

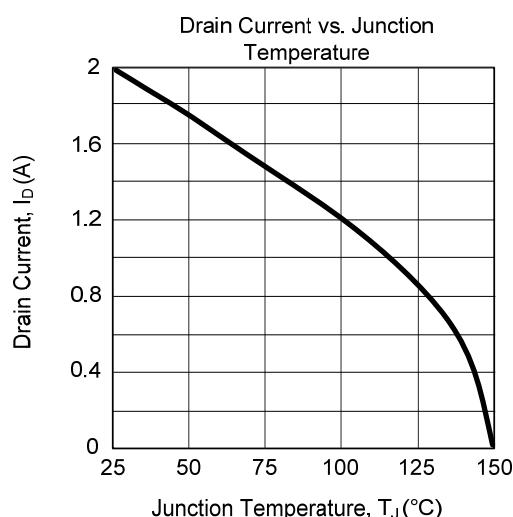
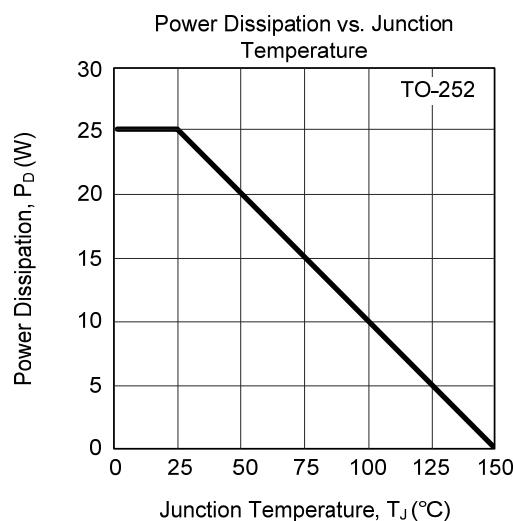
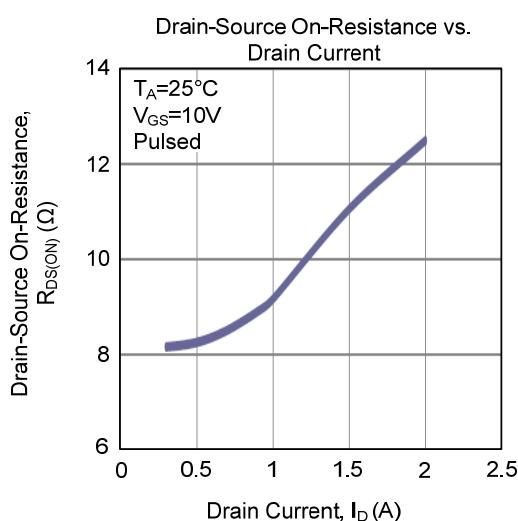
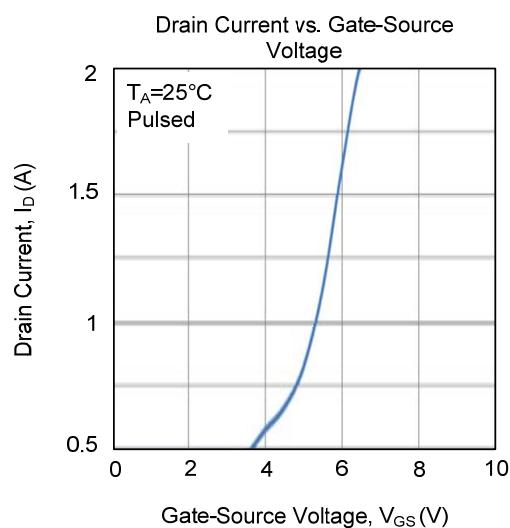
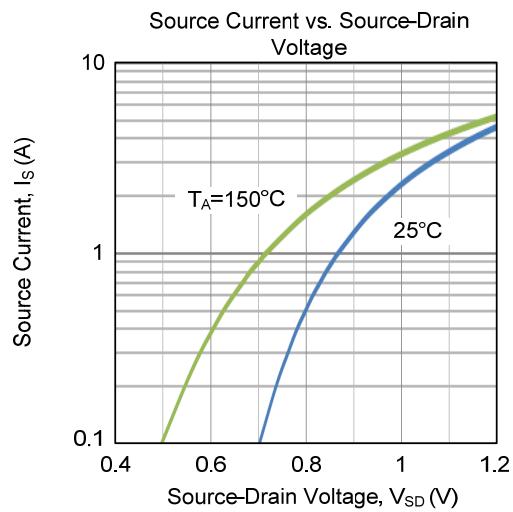
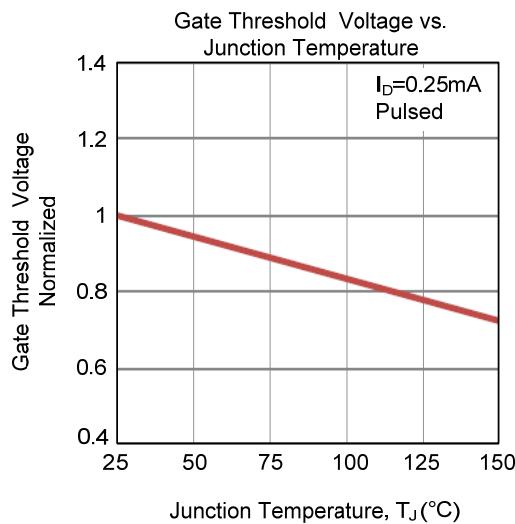


Unclamped Inductive Switching Waveforms

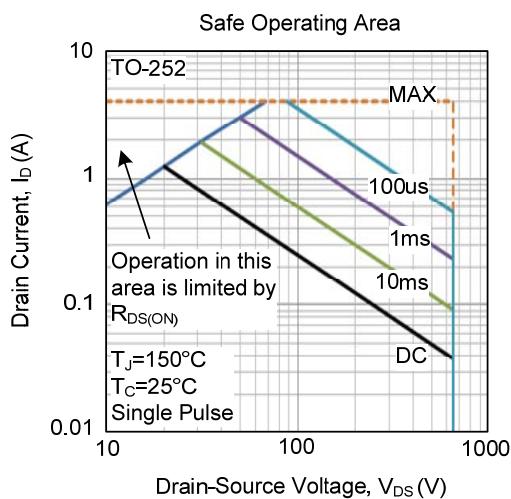
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



- TYPICAL CHARACTERISTICS (Cont.)



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